

L Number	Hits	Search Text	DB	Time stamp
-	3830	depletion and lateral and (mos or mosfet or pmos or pmosfet or nmos or nmosfet or cmos or cmosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 08:27
-	308	(257/402).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 13:15
-	2170	((257/240) or (257/244) or (257/288) or (257/343) or (257/348) or (257/391) or (257/396) or (257/402)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 13:15
-	114	((257/240) or (257/244) or (257/288) or (257/343) or (257/348) or (257/391) or (257/396) or (257/402)).CCLS.) and channel near12 (lower or deeper or depth) near12 (substrate or p-well or n-well or well)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 13:59
-	5	(US-6091116-\$ or US-6229188-\$ or US-6465842-\$ or US-5502322-\$).did. or (US-20010009292-\$).did.	USPAT; US-PGPUB	2002/11/14 13:59
-	4	((US-6091116-\$ or US-6229188-\$ or US-6465842-\$ or US-5502322-\$).did. or (US-20010009292-\$).did.) and depletion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 14:46
-	1	("6222234").PN.	USPAT	2002/11/14 15:18
-	91	(depletion adj mode or depletion-mode) near12 (cmos or cmosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 15:19
-	18	(depletion adj mode or depletion-mode) near12 (cmos or cmosfet).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 15:26
-	14	(depletion adj mode or depletion-mode) near12 (cmos or cmosfet).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 19:14
-	2	("5424226").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 20:17
-	5	((("6229188") or ("5424226") or ("6465842"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 20:17
-	3	((("6229188") or ("5424226") or ("6465842"))).PN.	USPAT	2002/11/14 20:17
-	2	("6229188").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 08:47
-	94	(resistivity or electric\$2 adj conductivity) near12 "10.sup.13" and semiconductor.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 13:01

-	35	buried adj channel near12 diffusion adj region and semiconductor.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 13:40
-	713	buried adj channel.ti,ab,clm. and semiconductor.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 13:41
-	37	buried adj channel.ti. and mosfet.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 15:32
-	567	(memory or switching).ti,ab,clm. and gate adj oxide near12 lower	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 15:38
-	200	(memory or switching).ti,ab,clm. and gate adj oxide near3 lower	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 16:37
-	3	flotox.ti,ab,clm. and cmos.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 16:55
-	18	((memory or switching).ti,ab,clm. and gate adj oxide near3 lower) and cmos.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 16:55
-	2	("5017979").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 19:56
-	603	depletion and EEPROM.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 19:56
-	176	depletion.ti,ab,clm. and EEPROM.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 19:56
-	55	depletion adj (region or type).ti,ab,clm. and EEPROM.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 20:02
-	1453	threshold adj voltage near12 impurity near12 (density or concentration)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 20:03
-	3	threshold adj voltage near3 impurity near3 (density or concentration) and eeprom.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 20:07
-	4	threshold adj voltage near3 impurity near3 (density or concentration) near3 (source or drain) and mosfet.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/28 20:08

-	131	(buried adj channel or buried-channel).ti,ab,clm. and mosfet.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 08:31
-	48	(buried adj channel or buried-channel).ti,ab,clm. and mosfet.ti,ab,clm. and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 08:32
-	25	(buried adj channel or buried-channel).ti,ab,clm. and mosfet.ti,ab,clm. and 257/\$6.ccls.	USPAT	2003/04/29 08:32
-	13	(buried adj channel or buried-channel).ti,ab,clm. and mosfet.ti,ab,clm. and 257/\$6.ccls. and gate adj (oxide or insulation or insulating).ti,ab,clm.	USPAT	2003/04/29 08:46
-	135	(257/216).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 08:48
-	78	((257/216).CCLS.) and (buried adj channel or buried-channel)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 09:20
-	19	(buried adj channel or buried-channel).ti,ab,clm. and trench.ti,ab,clm. and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 11:45
-	550	trench.ti,ab,clm. and (mos or mosfet).ti,ab,clm. and well.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 11:51
-	55	trench.ti,ab,clm. and (mos or mosfet).ti,ab,clm. and well.ti,ab,clm. and lateral.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 11:53
-	15	trench.ti,ab,clm. and (mos or mosfet).ti,ab,clm. and well.ti,ab,clm. and lateral near3 (mos or mosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 12:05
-	2	thickness near4 gate adj oxide.clm. and lateral adj mosfet.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 12:07
-	2	thickness near4 gate adj oxide.clm. and lateral adj (mos or mosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 12:08
-	3	thickness near4 gate adj (insulation or oxide).clm. and lateral adj (mos or mosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 12:10
-	3	(thick or thickness) near4 gate adj (insulation or oxide).clm. and lateral adj (mos or mosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 12:11

-	16	(thick or thickness) near4 gate adj (insulation or oxide) and lateral adj (mos or mosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 12:17
-	0	(thick or thickness) near4 gate adj (insulation or oxide) near4 ".ANG." and lateral adj (mos or mosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 12:13
-	0	(thick or thickness) near12 gate adj (insulation or oxide) near12 ".ANG." and lateral adj (mos or mosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 12:13
-	29	(thick or thickness) near4 gate adj (insulation or oxide) and lateral adj (cmos or nmos or pmos or nmosfet or pmosfet or dmos or dmosfet or ldmos or ldmosfet or mos or mosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 14:19
-	1	thick adj gate adj oxide and lateral adj mosfet.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 14:20
-	1	thick adj gate adj oxide and lateral adj (fet or mos or mosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 14:21
-	1	thick adj gate adj oxide and lateral adj (fiedl adj effect or fet or mos or mosfet or nmos or nmosfet or pmos or pmosfet or cmos or cmosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 14:22
-	14	simox.ti,ab,clm. and gate adj oxide near6 (thickness or thick)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 14:30
-	8	thick adj gate adj oxide near6 (thickness or thick) and mosfet.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 14:32
-	8	thick adj gate adj oxide near6 (thickness or thick) and (lateral adj field adj effect or mosfet).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 14:33
-	9	thick adj gate adj oxide near6 (thickness or thick or nm or ".ANG.") and (lateral adj field adj effect or mosfet).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 16:14
-	2	("6229188").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 15:20
-	2	("5424226").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 15:20
-	0	lateral adj (mos or mosfet).ti,ab,clm. and (buried adj channel or buried-channel) and epitaxial adj (region or layer) near12 well	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 16:56

-	27	advantage near5 depletion near5 enhancement	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 17:00
-	1	cost near5 depletion near5 enhancement	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 17:01
-	17	advantage near5 depletion-mode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 19:37
-	42	field adj oxide near3 (thick or thickness) and (buried-channel or buried adj channel) and gate adj oxide near4 (thick or thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 19:39
-	0	field adj oxide near3 (thick or thickness) and (buried-channel or buried adj channel) and gate adj oxide near4 (thick or thickness) and lateral adj mosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 19:39
-	39	field adj oxide near3 (thick or thickness) and (buried-channel or buried adj channel) and gate adj oxide near4 (thick or thickness) and (mos or mosfet or field adj effect adj transistor or cmos or cmosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 20:35
-	2	("5424226").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 21:20
-	1	"nec" and planar adj lower adj surface and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 20:38
-	4	"nec" and planar adj surface and cmos.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 20:38
-	2	("5622880").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/29 21:20